

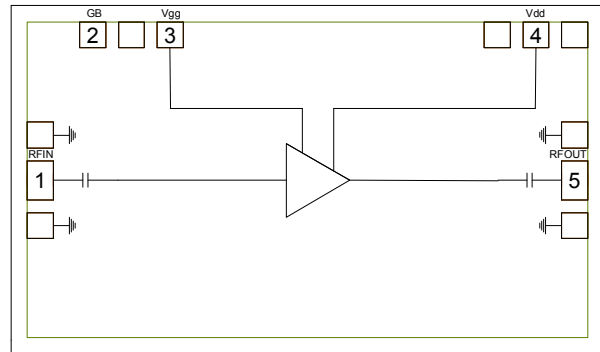
Features

- ▶ Low noise figure
- ▶ High gain broadband performance
- ▶ Low current consumption
- ▶ All positive bias
- ▶ Small die size

Description

The CMD229 is a broadband MMIC low noise amplifier ideally suited for microwave radios and C and X-band applications where high gain, low noise figure and low power consumption are needed. The broadband device delivers 27 dB of gain with a corresponding output 1 dB compression point of +13 dBm and a noise figure of 1.4dB. The CMD229 is a 50 ohm matched design eliminating the need for external DC blocks and RF port matching. The CMD229 offers full passivation for increased reliability and moisture protection.

Functional Block Diagram



Electrical Performance - $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, $F=8\text{ GHz}$

Parameter	Min	Typ	Max	Units
Frequency Range	5 - 11			GHz
Gain		27		dB
Noise Figure		1.4		dB
Input Return Loss		20		dB
Output Return Loss		10		dB
Output P1dB		13		dBm
Supply Current		45		mA

Specifications

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, V _{dd}	5.5 V
Gate Voltage, V _{gg}	5.5 V
RF Input Power	+20 dBm
Channel Temperature, T _{ch}	150 °C
Power Dissipation, P _{diss}	464 mW
Thermal Resistance	140 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V _{dd}	3.0	4.0	5.0	V
I _{dd}		45		mA
V _{gg}	3.0	4.0	5.0	V
I _{gg}		5		mA

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

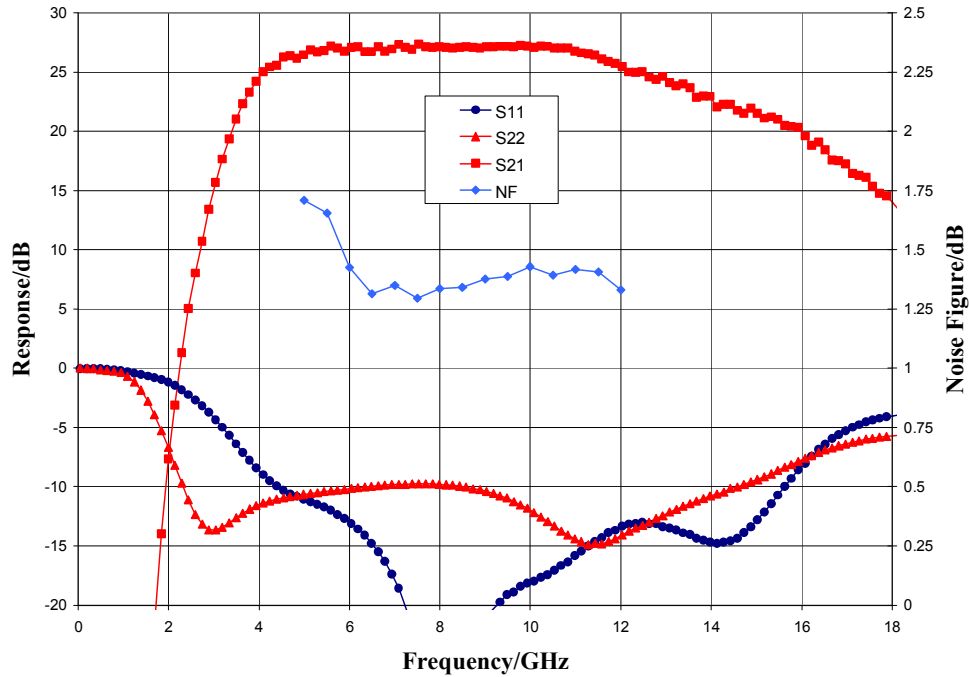
Electrical Specifications, V_{dd} = 4.0 V, V_{gg} = 4.0 V, T_A = 25 °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range	6 - 10			5 - 11			GHz
Gain	24	27	30	24.5	27	30	dB
Noise Figure		1.4	1.8		1.4	2.0	dB
Input Return Loss		15			13		dB
Output Return Loss		10			10		dB
Output P _{1dB}		13			13		dBm
Output IP ₃		25			25		dBm
Supply Current	30	45	60	30	45	60	mA
Gain Temperature Coefficient		0.012			0.012		dB/°C
Noise Figure Temperature Coefficient		0.007			0.007		dB/°C

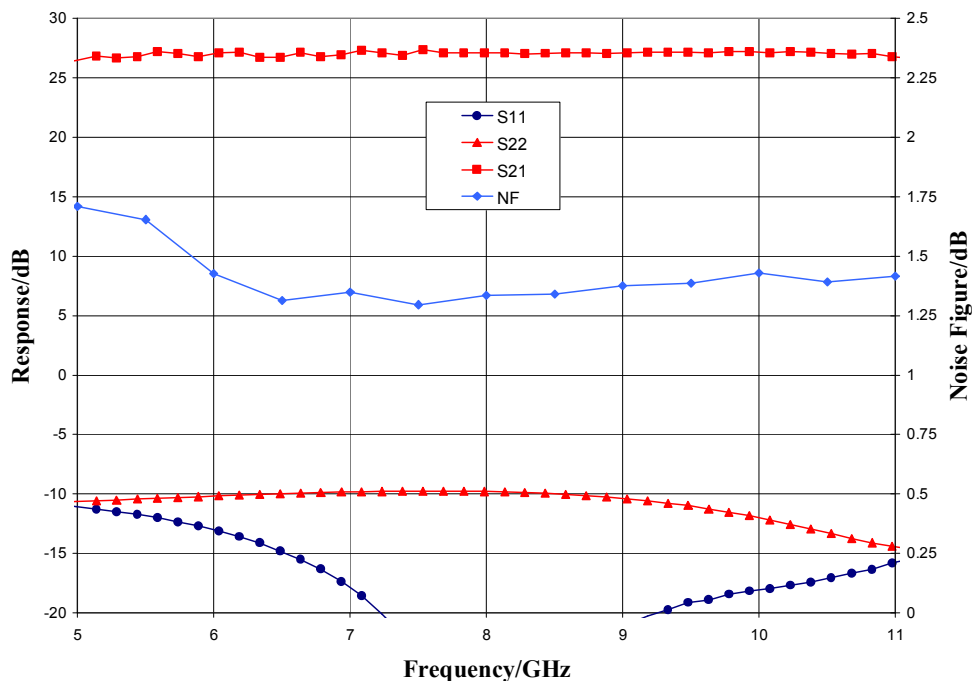
ver 1.1 0616

Typical Performance

Broadband Performance, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$, $I_{dd} = 45\text{mA}$, $T_A = 25\text{ }^\circ\text{C}$



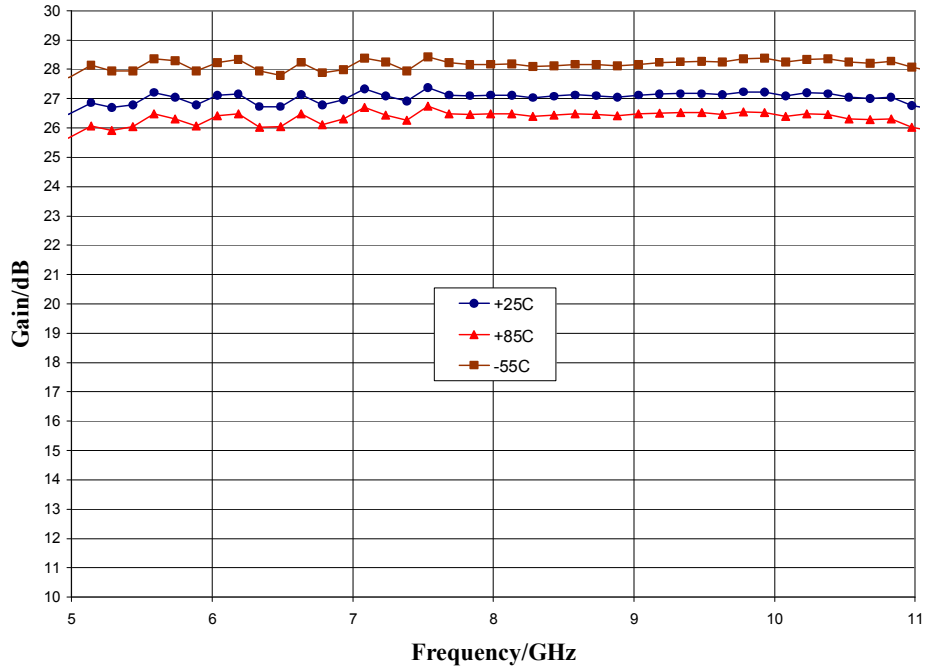
Narrow-band Performance, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$, $I_{dd} = 45\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



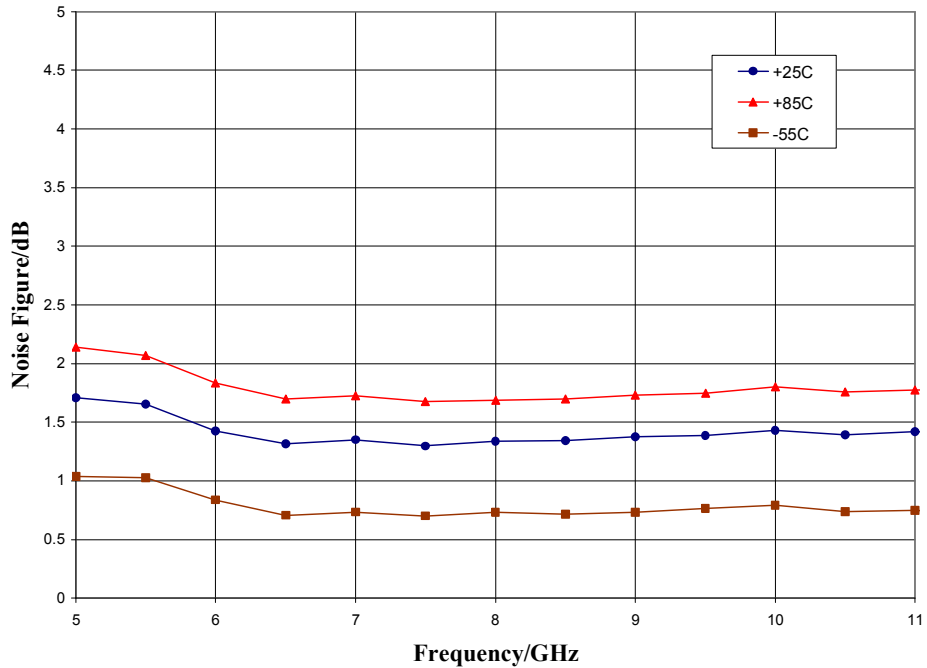
ver 1.1 0616

Typical Performance

Gain vs. Temperature, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$



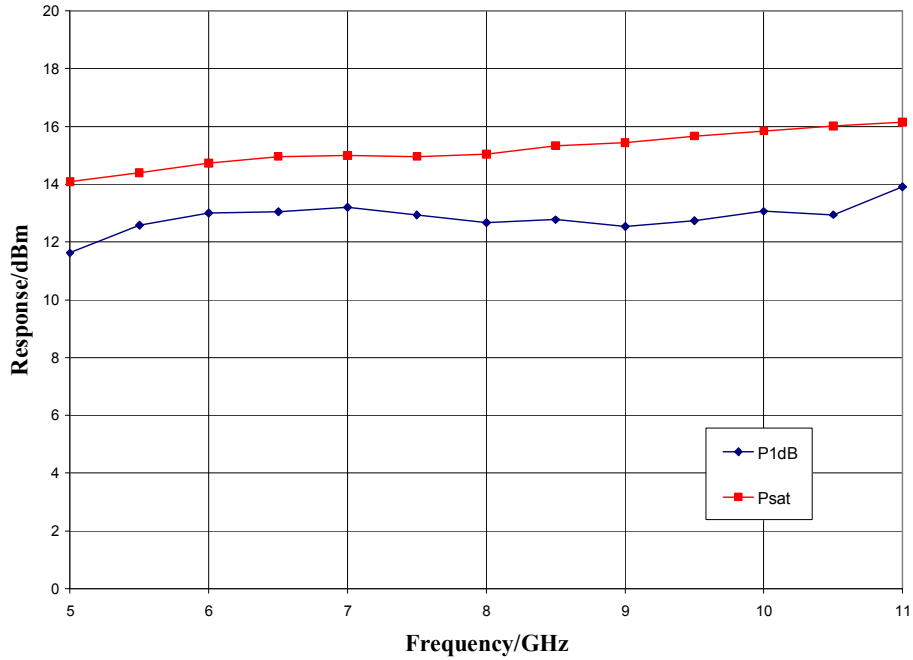
Noise Figure vs. Temperature, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$



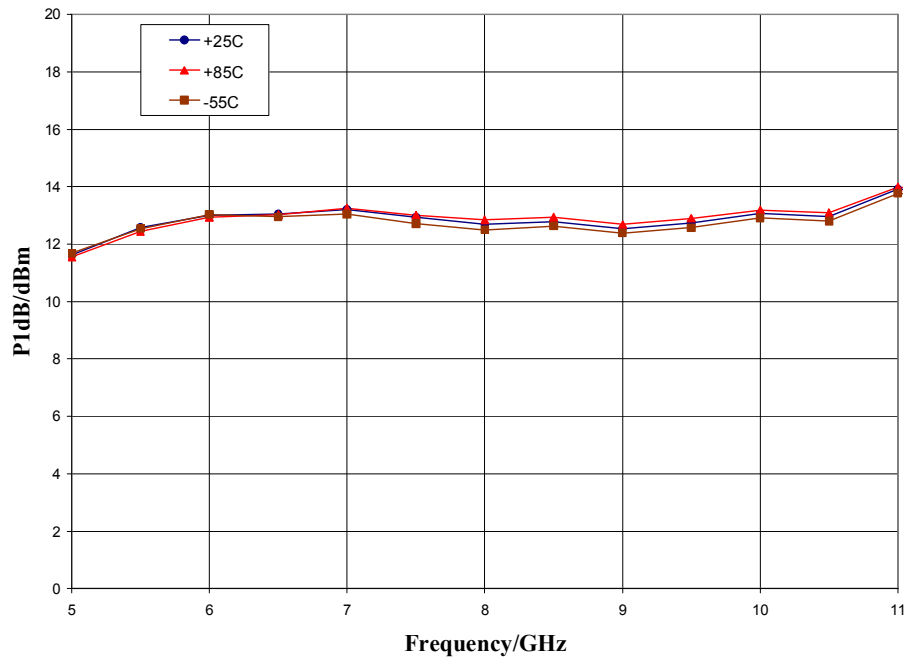
ver 1.1 0616

Typical Performance

Output Power, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$, $I_{dd} = 45\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



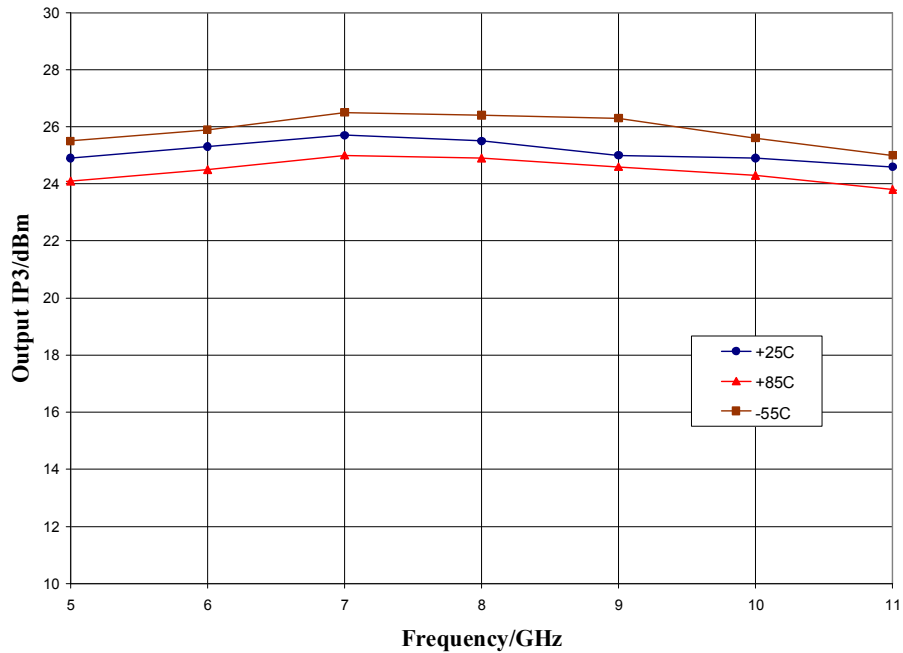
P1dB vs. Temperature, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$



ver 1.1 0616

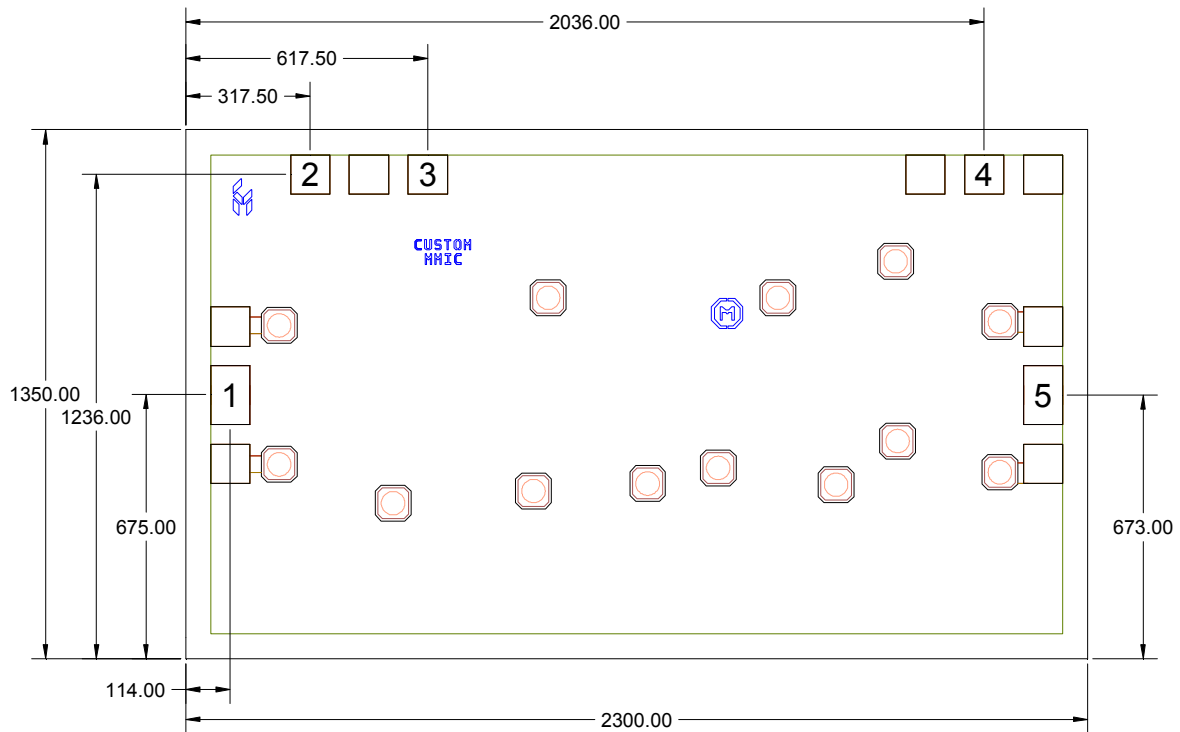
Typical Performance

Output IP3 vs. Temperature, $V_{dd} = 4.0\text{ V}$, $V_{gg} = 4.0\text{ V}$



Mechanical Information

Die Outline (all dimensions in microns)

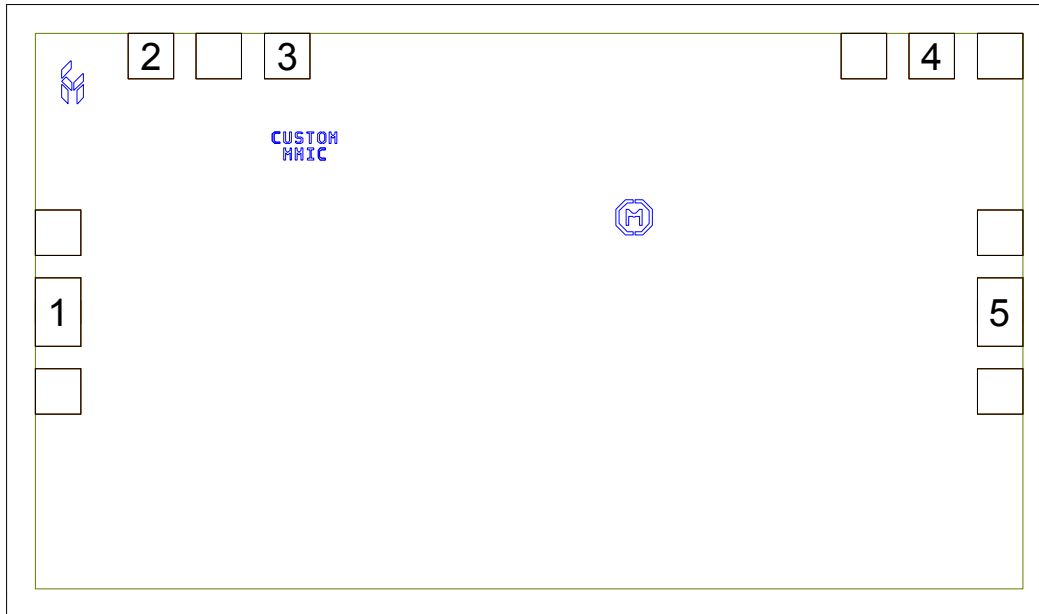


Notes:


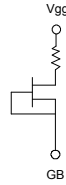
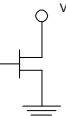


1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads are 100 microns square

Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC blocked and 50 ohm matched	
2	GB	Connect to DC ground	
3	Vgg	Power supply voltage Decoupling and bypass caps required	
4	Vdd	Power supply voltage Decoupling and bypass caps required	
5	RF out	DC blocked and 50 ohm matched	
Backside	Ground	Connect to RF / DC ground	

ver 1.1 0616

Applications Information

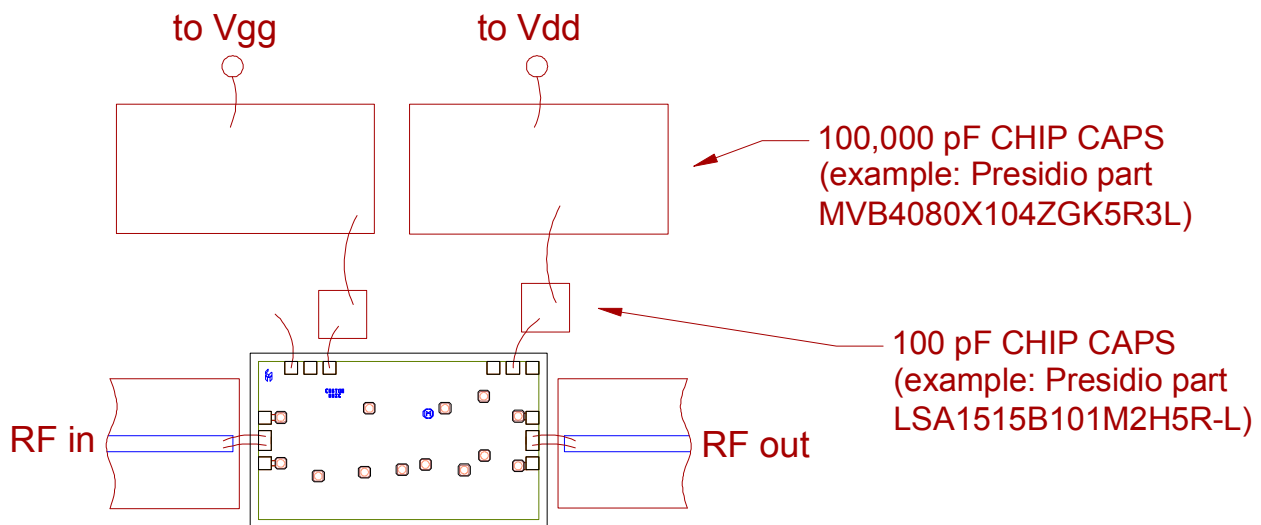
Assembly Guidelines

The backside of the CMD229 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

ver 1.1 0616

*Applications Information***Biasing and Operation**

The CMD228 is biased with a positive drain supply and positive gate supply. Performance is optimized when the drain voltage is set to +4.0 V, though it may be set to a minimum of +3.0 V and a maximum of +5.0 V. The recommended gate voltage is +4.0 V.

Turn ON procedure:

1. Apply drain voltage V_{dd} and set to +4 V
2. Apply gate voltage V_{gg} and set to +4 V

Turn OFF procedure:

1. Turn off gate voltage V_{gg}
2. Turn off drain voltage V_{dd}

RF power can be applied at any time.